# PNP Silicon Epitaxial Transistor

This PNP Silicon Epitaxial Transistor is designed for use in low voltage, high current applications. The device is housed in the SOT-223 package, which is designed for medium power surface mount applications.

## **Features**

- High Current:  $I_C = -1.0 \text{ A}$
- The SOT-223 Package can be soldered using wave or reflow.
- SOT-223 package ensures level mounting, resulting in improved thermal conduction, and allows visual inspection of soldered joints.
   The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die.
- NPN Complement is BCP68
- Pb-Free Package is Available

## **MAXIMUM RATINGS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-20	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-25	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current	Ic	-1.0	Adc
Total Power Dissipation @ T <sub>A</sub> = 25°C (Note 1) Derate above 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to 150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance – Junction-to-Ambient (Surface Mounted)	$R_{\theta JA}$	83.3	°C/W
Lead Temperature for Soldering, 0.0625 in from case	TL	260	°C
Time in Solder Bath		10	Sec

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

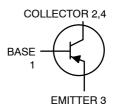
Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 sq. in.

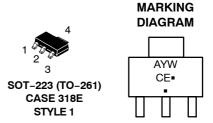


## ON Semiconductor®

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# MEDIUM POWER PNP SILICON HIGH CURRENT TRANSISTOR SURFACE MOUNT





CE = Specific Device Code A = Assembly Location

Y = Year
W = Work Week
Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BCP69T1	SOT-223	1000 / Tape & Reel
BCP69T1G	SOT-223 (Pb-Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = –100 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CES</sub>	-25	-	_	Vdc	
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-20	-	-	Vdc	
Emitter-Base Breakdown Voltage ( $I_E = -10 \mu Adc$ , $I_C = 0$ )	V <sub>(BR)EBO</sub>	-5.0	-	-	Vdc	
Collector-Base Cutoff Current (V <sub>CB</sub> = -25 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-	-10	μAdc	
Emitter-Base Cutoff Current (V <sub>EB</sub> = -5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-	-10	μAdc	
ON CHARACTERISTICS						
DC Current Gain ( $I_C = -5.0$ mAdc, $V_{CE} = -10$ Vdc) ( $I_C = -500$ mAdc, $V_{CE} = -1.0$ Vdc) ( $I_C = -1.0$ Adc, $V_{CE} = -1.0$ Vdc)	h <sub>FE</sub>	50 85 60	- - -	- 375 -	-	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = -1.0 Adc, I <sub>B</sub> = -100 mAdc)	V <sub>CE(sat)</sub>	-	-	-0.5	Vdc	
Base–Emitter On Voltage (I <sub>C</sub> = -1.0 Adc, V <sub>CE</sub> = -1.0 Vdc)	V <sub>BE(on)</sub>	-	-	-1.0	Vdc	
DYNAMIC CHARACTERISTICS						
Current-Gain - Bandwidth Product (I <sub>C</sub> = -10 mAdc, V <sub>CE</sub> = -5.0 Vdc)	f <sub>T</sub>	-	60	_	MHz	

# TYPICAL ELECTRICAL CHARACTERISTICS

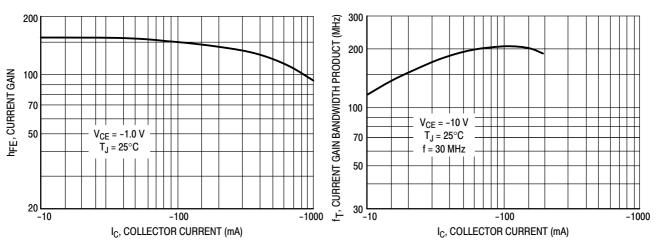


Figure 1. DC Current Gain

Figure 2. Current Gain Bandwidth Product

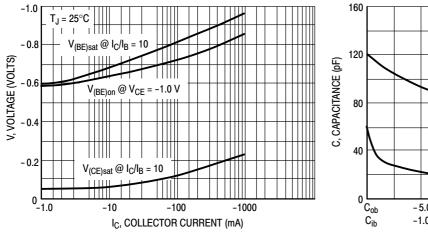


Figure 3. Saturation and "ON" Voltages

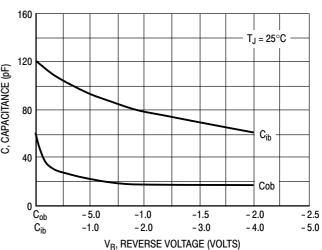


Figure 4. Capacitances

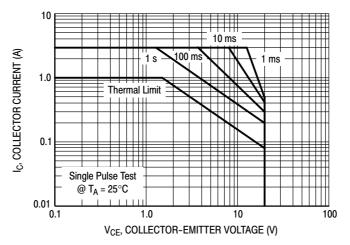
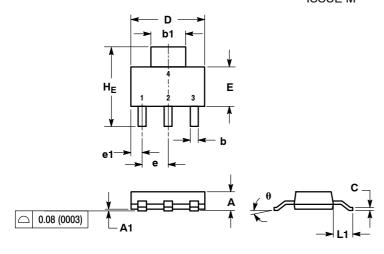


Figure 5. Safe Operating Area

## PACKAGE DIMENSIONS

## **SOT-223 (TO-261)** CASE 318E-04 ISSUE M



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI

Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
С	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
е	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°

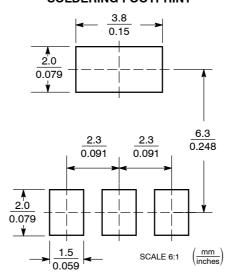
STYLE 1:

PIN 1. BASE 2. COLLE

2. COLLECTOR 3. FMITTER

EMITTER
 COLLECTOR

## SOLDERING FOOTPRINT



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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